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## FORM HDP-1449 (Based on Form PTO-1449)

## PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)

Sheet 1 of 1

ATTORNEY DOCKET No.	SERIAL NO.
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APPLICANT	
Masayasu MIYATA	
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U.S. PATENT DOCUMENTS						
Ref. Desig.	Examiner's Initials	Document Number	Date	Name	Class/ Subclass	(If appropriate) Filing Date
1.		6,821,566	11/23/2004	Nakamura et al.		

FOREIGN PATENT DOCUMENTS							
Ref. Desig.	Examiner's Initials	Document Number	Date	Country	Class/ Subclass	Translation Yes	* No
1.		JP10-223628	08/21/1998	Japan		Abstract	
2.		JP2001-148381	05/29/2001	Japan		Abstract	

OTHE	OTHER DOCUMENTS (including Author, Title, Date, Pertinent Pages, etc.)				
Ref. Desig.	Examiner's Initials				
1.		G. D. Wilk et al., Stable zirconium silicate gate dielectrics deposited directly on silicon, Applied Physics letters, U.S.A., american Institute of Physics, January 3, 2000, Vol. 76, Number 1, 112-114.			
2.		M. Quevedo-Lopez et al., Hafnium interdiffusion studies from hafnium silicate into silicon, Applied Physics Letters, U.S.A., American Institute of Physics, December 17, 2001, Vol. 79, Number 25, 4192-4194.			
3.		G.D.Wilk, et al., Electrical properties of hafnium silicate gate dielectrics deposited directly on silicon, Applied Physics Letters, U.S.A., American Institute of Physics, May 10, 1995, Vol. 74, Number 19, 2854-2856.			
4.		Shin-ichi Saito et. al., Inversion Electron Mobility Affected by Phase Separation in Hgih- Permittivity Gate Dielectrics, Jpn. J. Appl. Phys., Japan, The Japan Society of Applied Physics, December 1, 2003, Part 2, No. 12A, Vol. 42 (2003), L1425-L1428			

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Examiner: /Phat Cao/ Date Considered: 12/30/2009